

isc N-Channel MOSFET Transistor

STW4N150

FEATURES

- Drain Current I_D: 4.0A@ T_C=25°C
- Drain Source Voltage-
- : V_{DSS}= 1500V(Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 7.0 \Omega (Max)$
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

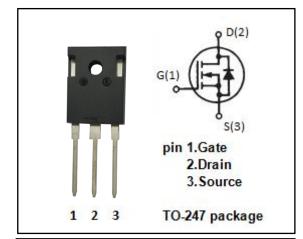
- · High speed power switching
- Switching regulator, DC-DC converter

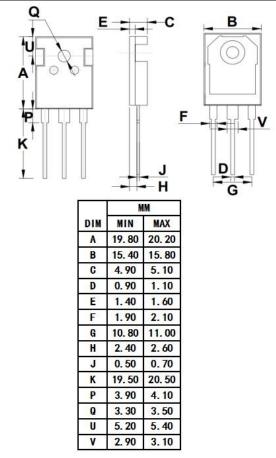
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	1500	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous	4.0	А
I _{DM}	Drain Current-Single Pulsed	12	А
P _D	Total Dissipation @T _C =25°C 160		W
Tj	Max. Operating Junction Temperature 150		$^{\circ}$
T _{stg}	Storage Temperature	rage Temperature -55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.78	°C/W





isc website: www.iscsemi.cn

isc & iscsemi is registered trademark



isc N-Channel MOSFET Transistor

STW4N150

ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V; ID = 1.0mA	1500		V
V _{GS} (th)	Gate Threshold Voltage	$V_{DS} = V_{GS}$; ID = 0.25mA	3.0	5.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D = 2A		7.0	Ω
Igss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V		±0.1	μА
I _D ss	Drain-Source Leakage Current	V _{DS} = 1500V; V _{GS} = 0V		10	μА
V _{SD}	Diode forward voltage	I _F = 4.0A; V _{GS} = 0V		2.0	V

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications. ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.cn

isc & iscsemi is registered trademark